

TO-92 Plastic-Encapsulate Transistors

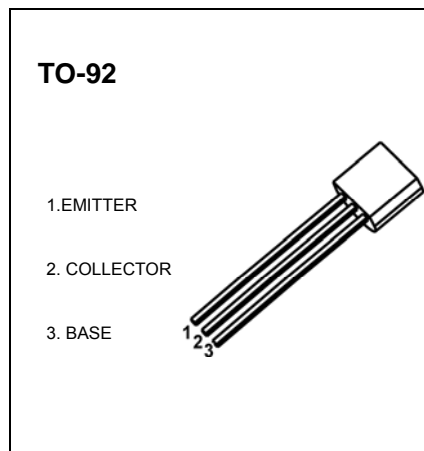
2SA950 TRANSISTOR (PNP)

FEATURES

- 1W Output Applications
- Complementary to 2SC2120

MAXIMUM RATINGS (T_a=25 °C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-35	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.8	A
P _C	Collector Power Dissipation	0.6	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55 to +150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.1mA, I _E =0	-35			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -0.1mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -35V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-100mA	100		320	
	h _{FE(2)}	V _{CE} =-1V, I _C = -700mA	35			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -500mA, I _B = -20mA			-0.7	V
Emitter-base voltage	V _{BE}	V _{CE} =-1V, I _C =-10mA	-0.5		-0.8	V
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0 f=1MHz		19		pF
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA		120		MHz

CLASSIFICATION OF h_{FE(1)}

Rank	O	Y
Range	100-200	160-320

